# High Voltage Full Bridge Drive ICs SLA2402MS

#### **■**Features

- •One Package Full Bridge Driver Consisted of High Voltage IC and Power MOSFETs(4 pieces)
- •High Voltage Driver which accepts direct connection to the input sgnal line
- •External components such as high voltage diodes and capacitors are not required

# ■Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Conditions
Power source voltage *	VM	500	٧	
Input voltage	VIN	15	V	
Output voltage	Vo	500	V	Pw≦250μs Without heatsink
Output current	lo	15	A W	
Power dissipation	PD	5 (Ta=25°C)		
Storage temperature	Tstg	-40 to +125	°C	
Operation temperature	Topr	-40 to +105	°C	

<sup>\*</sup> Power GND (D terminal) to -HV (-HV terminal) voltage.

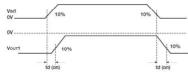
#### **■**Electrical Characteristics

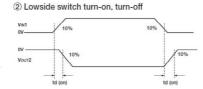
Parameter	Symbol -	Ratings			Unit	Conditions
		min	typ	max	Offic	Conditions
Power MOS FET output breakdown voltage	BV <sub>out</sub>	500			V	Ιο-100μΑ
Power MOS FET output leakage voltage	IOUT (off)			100	μA	V <sub>0</sub> =500V
High-side Power MOS FET output on-state voltage	Vour (on) 1	0.28	0.4	0.52	V	I <sub>O</sub> =0.4A, V <sub>IN</sub> =10V
	V <sub>OUT (on)</sub> 2	1.4	2.0	2.6	V	Io=2A, V <sub>IN</sub> =10V
Low-side Power MOS FET output on-state voltage	Vour (on) 1	0.28	0.4	0.52	٧	I <sub>O</sub> =0.4A, V <sub>GL</sub> =10V
	Vour (on) 2	1.4	2.0	2.6	٧	I <sub>O</sub> =2A, V <sub>GL</sub> =10V
Quiescent circuit current	Icc 1			3.0	mA	V <sub>CC</sub> =4.5 to 15V
	Icc 2			4.0	mA	V <sub>CC</sub> =10V, V <sub>M</sub> =400V
Operating circuit current	Icc 3			4.0	mA	Vcc=10V, VM=400V
Input voltage (High level)	VIH	0.8V <sub>CC</sub>			V	V <sub>CC</sub> =4.5 to 15V
Input voltage (Low level)	VIL			0.2Vcc	V	V <sub>CC</sub> =4.5 to 15V
Delay time *	t <sub>d</sub> (on)		1.4		μs	V <sub>CC</sub> =10A, V <sub>IN</sub> =10V, V <sub>M</sub> =85A, I <sub>O</sub> =0.41A
	td (off)		3.3		μs	
	Δt			2.5	μs	
Operating voltage	Vcc			15	V	-40 to +105°C

\* About delay time

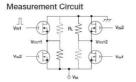
Signal input waveform vs output waveform

1 Highside switch turn-on, turn-off





\*  $\Delta t$ :  $\Delta t = td$  (on) – td (off)

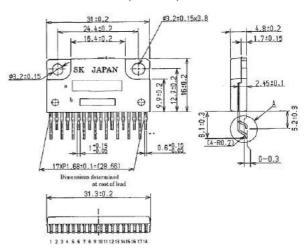


Conditions V<sub>CC</sub>=10V, V<sub>IN</sub>=10V (pulse) V<sub>M</sub>=85V I<sub>O</sub>=0.41A (R<sub>L</sub>=207Ω)

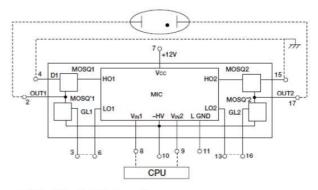
\* When pulse signal is inputted to Vint, RL on solid line is ON and dotted line RL is off.

On the contrary, when pulse signal is inputted to  $V_{IN2}$ ,  $R_L$  on dotted line is ON and dotted line  $R_L$  is off.

#### ■External Dimensions (unit:mm)

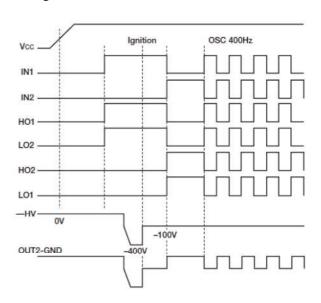


# ■Block Diagram



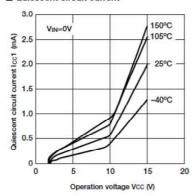
\* Dotted Line: Outside Connection

#### **■**Timing Chart

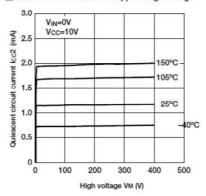


# **Electrical Characteristics**

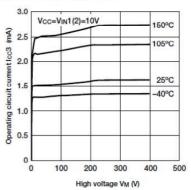
#### ■ Quiescent circuit current



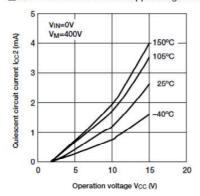
#### ■ Quiescent circuit current supplied high voltage



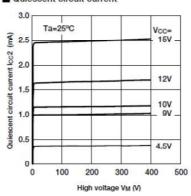
#### Operating circuit current



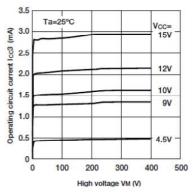
# ■ Quiescent circuit current supplied high voltage



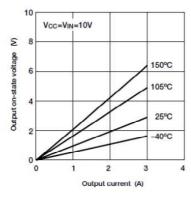
# Quiescent circuit current



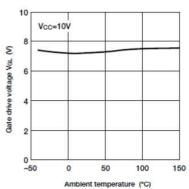
Operating circuit current



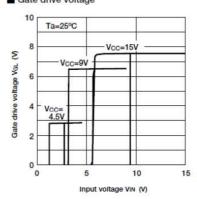
#### ■ Output on-state voltage



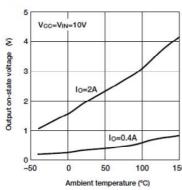
#### Gate drive voltage



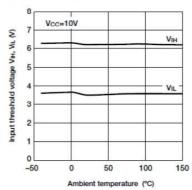
Gate drive voltage



#### Output on-state voltage

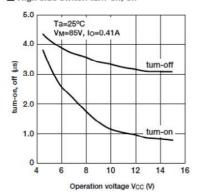


Input threshold voltage

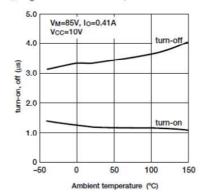


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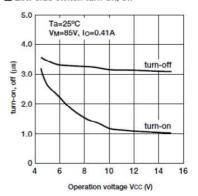
# ■ High side switch turn-on, off



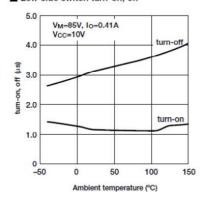
#### ■ High side switch turn-on, off



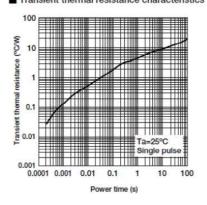
#### Low side switch turn-on, off



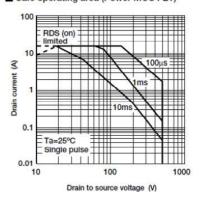
#### Low side switch turn-on, off



#### ■ Transient thermal resistance characteristics



#### Safe operating area (Power MOS FET)



# ■ Power derating curve

